

isc Silicon NPN Power Transistor**BU408****DESCRIPTION**

- High Voltage: $V_{CEV} = 400V(\text{Min})$
- Fast Switching Speed-
: $t_f = 400ns(\text{Max})$
- Low Saturation Voltage-
: $V_{CE(sat)} = 1.0V(\text{Max}) @ I_C = 6A$

APPLICATIONS

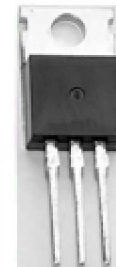
- Designed for use in horizontal deflection output stages of TV's and CRT's

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

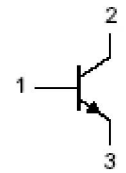
SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEV}	Collector-Emitter Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CP}	Collector Current-Peak Repetitive	10	A
I_{CP}	Collector Current- Peak (10ms)	15	A
I_B	Base Current	4	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	2.08	$^\circ\text{C/W}$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	70	$^\circ\text{C/W}$



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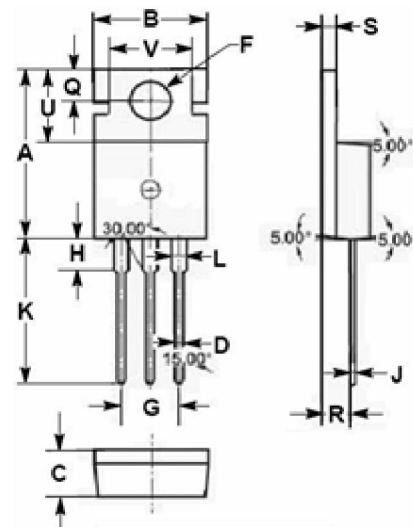


PIN 1. BASE

2. COLLECTOR

3. EMITTER

TO-220C package



DIM	mm	
	MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

isc Silicon NPN Power Transistor**BU408****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 100mA ; I _B = 0	200			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.2	V
I _{CES}	Collector Cutoff Current	V _{CE} = 400V; V _{BE} = 0 V _{CE} =250V; V _{BE} = 0 V _{CE} =250V; V _{BE} = 0; T _C = 150°C			5.0 0.1 1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C =0			1.0	mA
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A ; V _{CE} = 10V	10			MHz
t _f	Fall Time	I _C = 6A; I _{B1} = -I _{B2} = 1.2A			0.4	μs